

in a single etching step to the electrically conducting layer using only the mixed gas as the etchant.”

In the claims:

Amend claim 1 as follows:

1. (Thrice Amended) A semiconductor device manufacturing method comprising the steps of:

providing a semiconductor substrate having a lower electrically conducting layer thereon and an electrically insulating layer disposed over said electrically conducting layer;

providing a gas etchant comprising a mixed gas of [multiple] two different fluorocarbon gases, one of said fluorocarbon gases having a low carbon atoms to fluorine atoms ratio (hereinafter C/F ratio) and the other of said gases having a high C/F ratio, [each fluorocarbon gas having a different ratio of carbon atoms to fluorine atoms,] the fluorocarbon gas having the lower ratio of carbon atoms to fluorine atoms forming at least one half of the mixed gas; and

etching a connection hole through said electrically insulating layer in a single etching step to said electrically conducting layer using only said mixed gas as the etchant.

REMARKS

The specification has been added to include the subject matter of originally filed claims 1 and 2. Since claims 1 and 2 were originally filed, the addition to the specification is not new matter.

Claim 1 has been amended. Accordingly, claims 1 and 3 to 7 remain active in this application.